PROTON-ELECTROTEX
RUSSIA

High forward current capability
Low forward losses
Low thermal resistance
High load cycle capability

Rectifier Diode
For Welding
Type D266-12500-4

Average forward current		I_{FAV}	12500 A
Repetitive peak reverse voltage		V_{RRM}	200...400 V
V_{RRM}, V	200		400
Voltage code	2		4
T_j, °C	–45...+180		

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{FAV}	Maximum allowable average forward current[1)]	A	12500 15977	T_c= 113 °C; Double side cooled; T_c= 85 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FRMS}	RMS forward current	A	19625	T_c= 113 °C; Double side cooled; 180° half-sine wave; 50 Hz	
I_{FSM}	Surge forward current	kA	95.0 114.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_R=0 V
			100.0 120.0	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_R=0 V
I^2t	Safety factor	$A^2s\cdot10^3$	45100 64900	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=10 ms; single pulse; V_R=0 V
			41500 59700	T_j=$T_{j\,max}$ T_j=25 °C	180° half-sine wave; t_p=8.3 ms; single pulse; V_R=0 V
BLOCKING					
V_{RRM}	Repetitive peak reverse voltages	V	200...400	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; 50 Hz	
V_{RSM}	Non-repetitive peak reverse voltages	V	300...500	$T_{j\,min}$< T_j <$T_{j\,max}$; 180° half-sine wave; single pulse	
V_R	Reverse continuous voltages	V	0.6·V_{RRM}	T_j=$T_{j\,max}$	
THERMAL					
T_{stg}	Storage temperature	°C	–45...+40		
T_j	Operating junction temperature	°C	–45...+180		
MECHANICAL					
F	Mounting force	kN	35.0...70.0		
a	Acceleration	m/s^2	50	Device clamped	

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{FM}	Peak forward voltage, max	V	1.04 0.92	T_j=25 °C; I_{FM} = 6300 A T_j=$T_{j\,max}$; I_{FM} = 8000 A	
$V_{F(TO)}$	Forward threshold voltage, max	V	0.82 0.76	T_j=$T_{j\,max}$	19600 A < I_T < 58900 A 10000 A < I_T < 30000 A
r_T	Forward slope resistance, max	mΩ	0.018 0.019	T_j=$T_{j\,max}$	19600 A < I_T < 58900 A 10000 A < I_T < 30000 A
BLOCKING					
I_{RRM}	Repetitive peak reverse current, max	mA	50	T_j=$T_{j\,max}$; V_R=V_{RRM}	
SWITCHING					
Q_{rr}	Total recovered charge, max	μC	1250	T_j=$T_{j\,max}$; I_{FM}=1000 A; dI_{FM}/dt=-30 A/μs; V_R=100 B	
			780	T_j=$T_{j\,max}$; I_{FM}=1000 A; dI_{FM}/dt=-10 A/μs; V_R=100 B	
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	°C/W	0.0039	Direct Current	Double side cooled
R_{thjc-A}			0.0052		Anode side cooled
R_{thjc-K}			0.0150		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max		0.0030	Direct Current	
MECHANICAL					
m	Weight, max	g	145		
D_s	Surface creepage distance	mm (inch)	2.0 (0.079)		
D_a	Air strike distance	mm (inch)	2.0 (0.079)		

PART NUMBERING GUIDE

D	266	12500	4	N
1	2	3	4	5

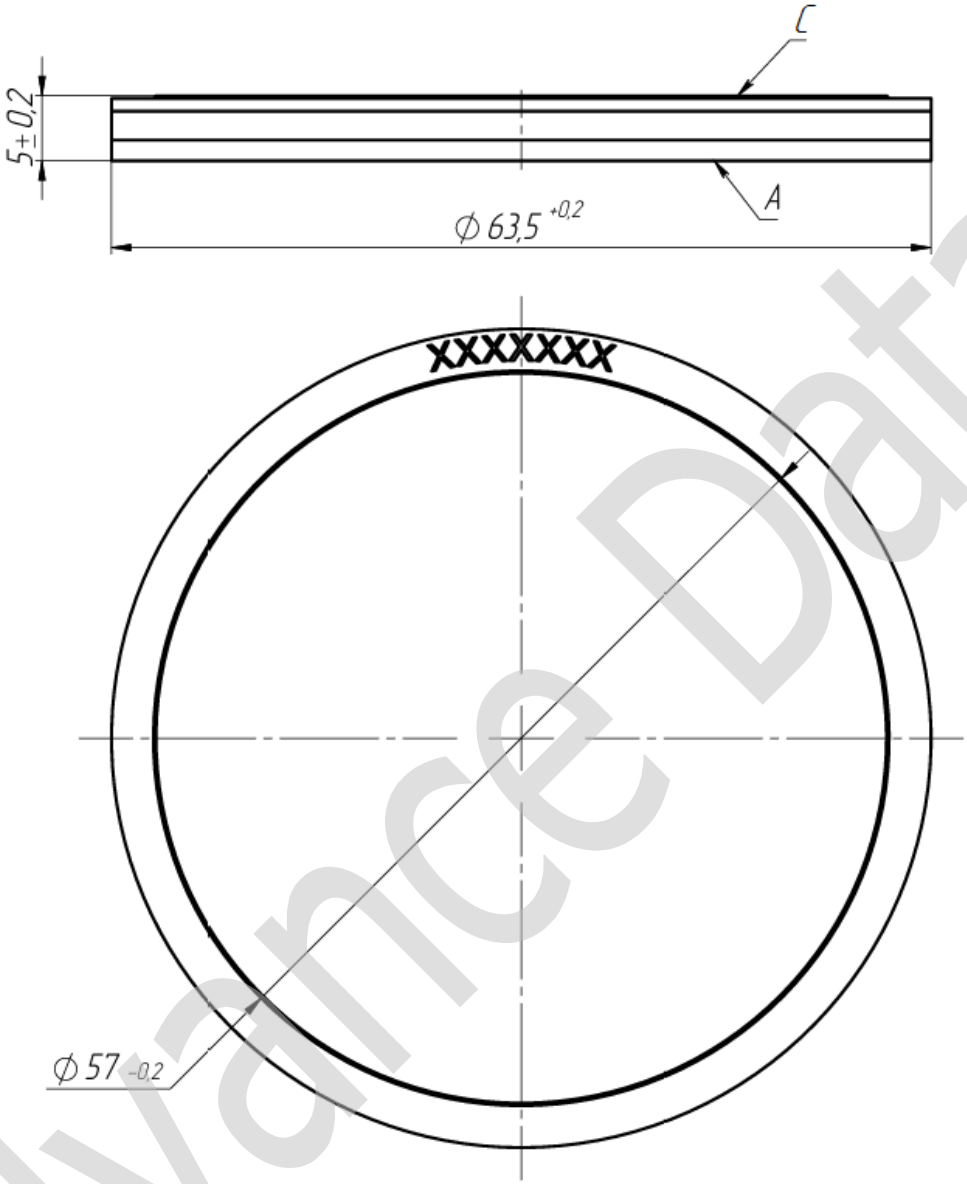
1. Device type: D – Diode
2. Design version
3. Maximum allowable average forward current, A
4. Voltage code
5. Ambient conditions: N – normal

NOTES

[1)] Calculation at $U_{F(TO)}$ / r_T in the range 19600 A<I_T<58900 A

OVERALL DIMENSIONS

Package type: HOUSINGLESS



All dimensions in millimeters

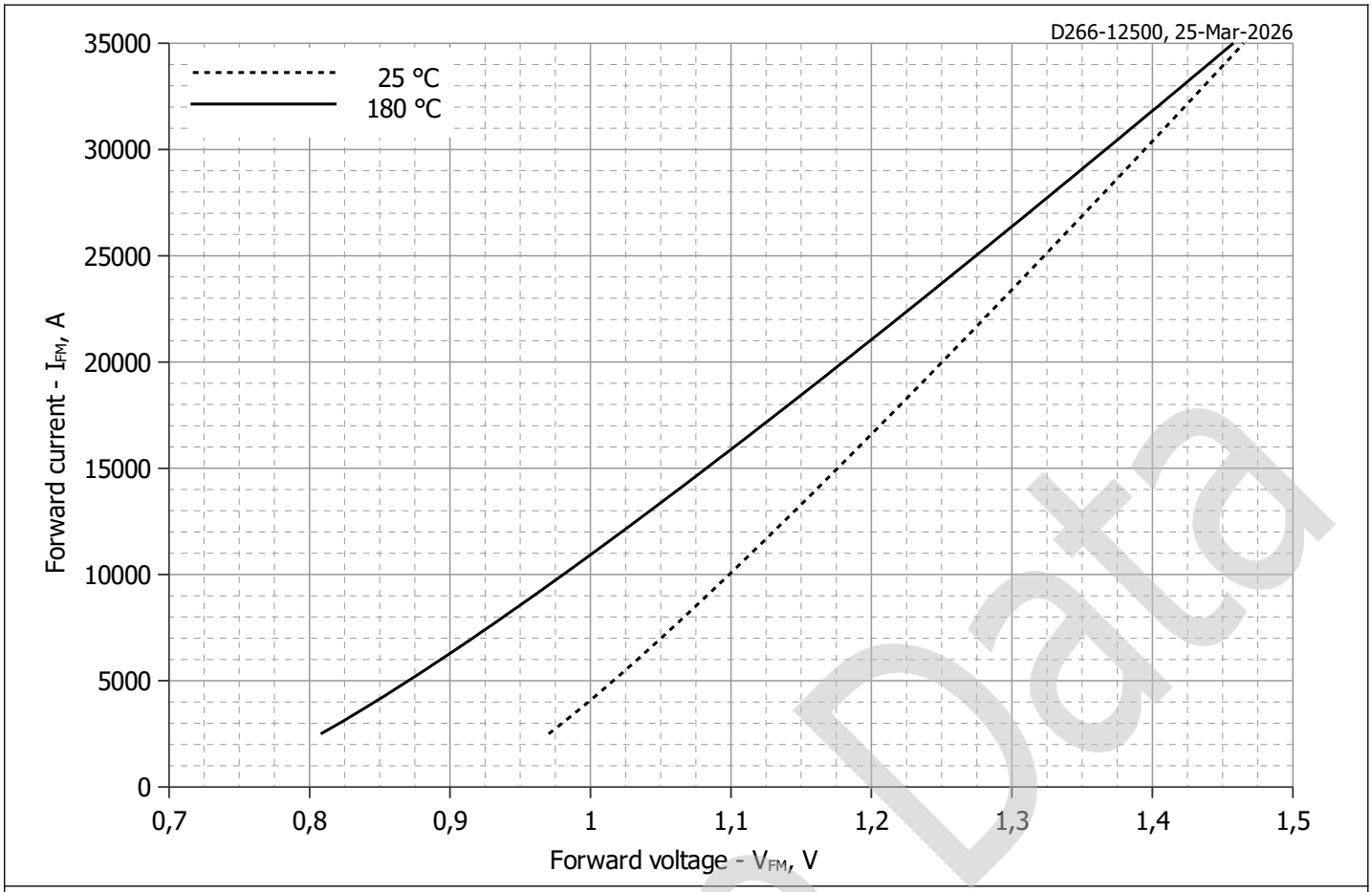


Fig 1 – Forward characteristics of Limit device

Analytical function for Forward characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	T_j = 25°C	$T_j = T_{j\,max}$
A	0.89993366	0.72931167
B	0.00001195	0.00001444
C	0.00023016	-0.00337811
D	0.00077210	0.00138075

Forward characteristic model (see Fig. 1).

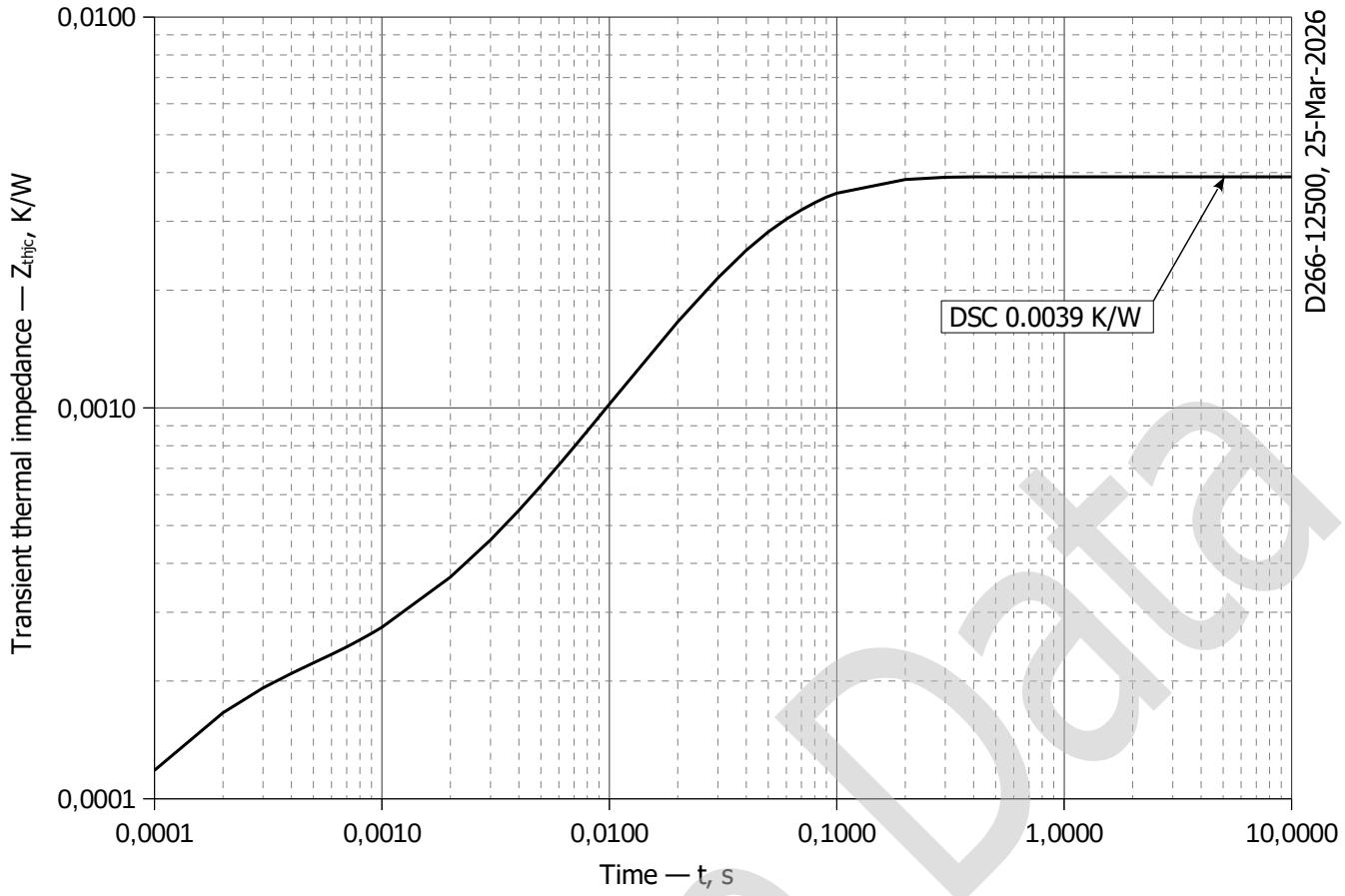


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^{n} R_i \left(1 - e^{-\frac{t}{\tau_i}}\right)$$

Where ***i*** = 1 to ***n***, ***n*** is the number of terms in the series.

t = Duration of heating pulse in seconds.
Z_{thjc} = Thermal resistance at time t.
R_i = Amplitude of p_{th} term.
τ_i = Time constatnt of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i, K/W	0.0006931	0.003018	0.000008917	0.00001092	0.0001425	0.0000266
τ_i, s	0.07563	0.03513	0.003417	0.0004864	0.000118	0.00003592

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

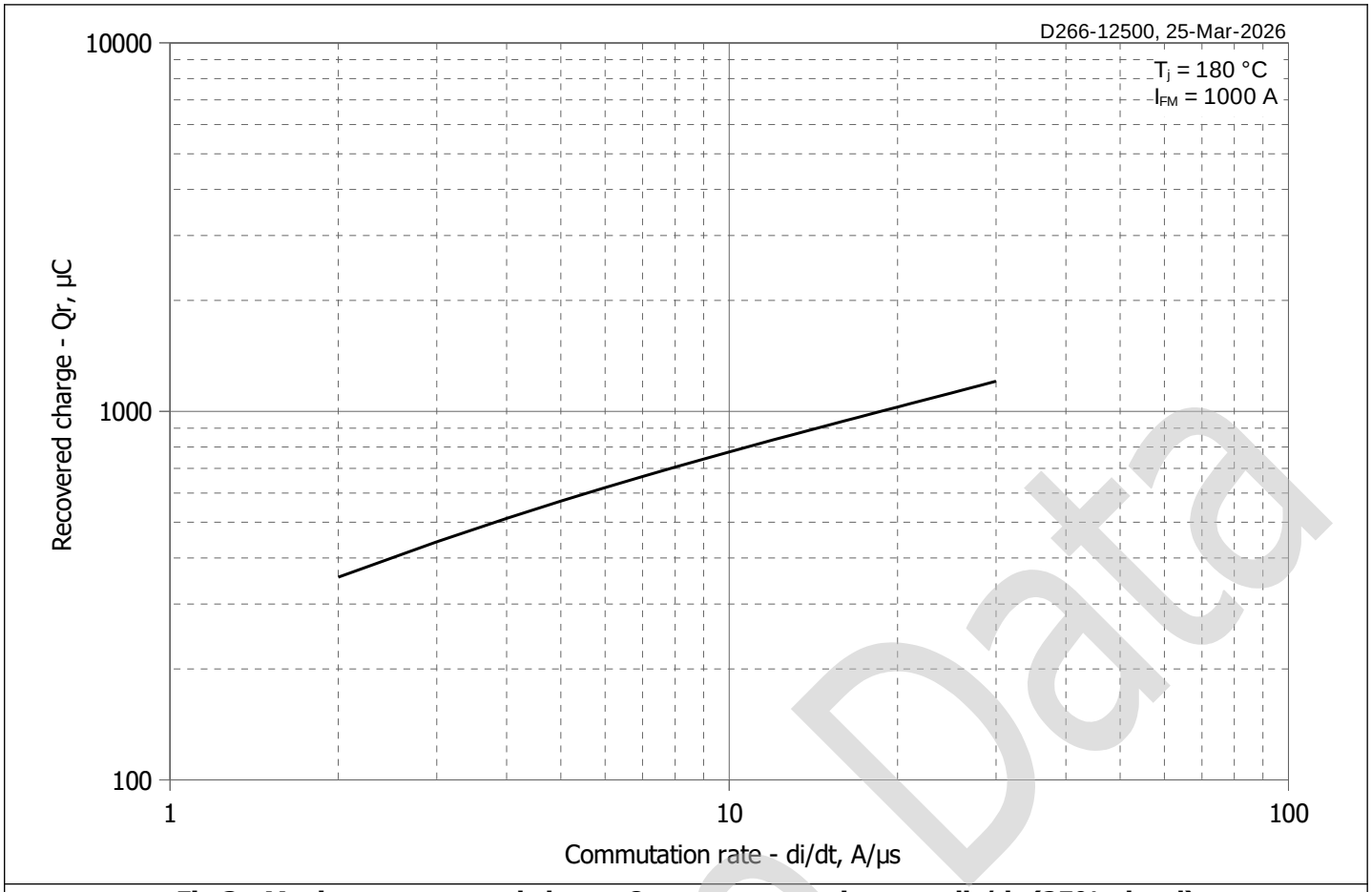


Fig 3 - Maximum recovered charge Q_{rr} vs. commutation rate di_R/dt (25% chord)

Fig 4 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

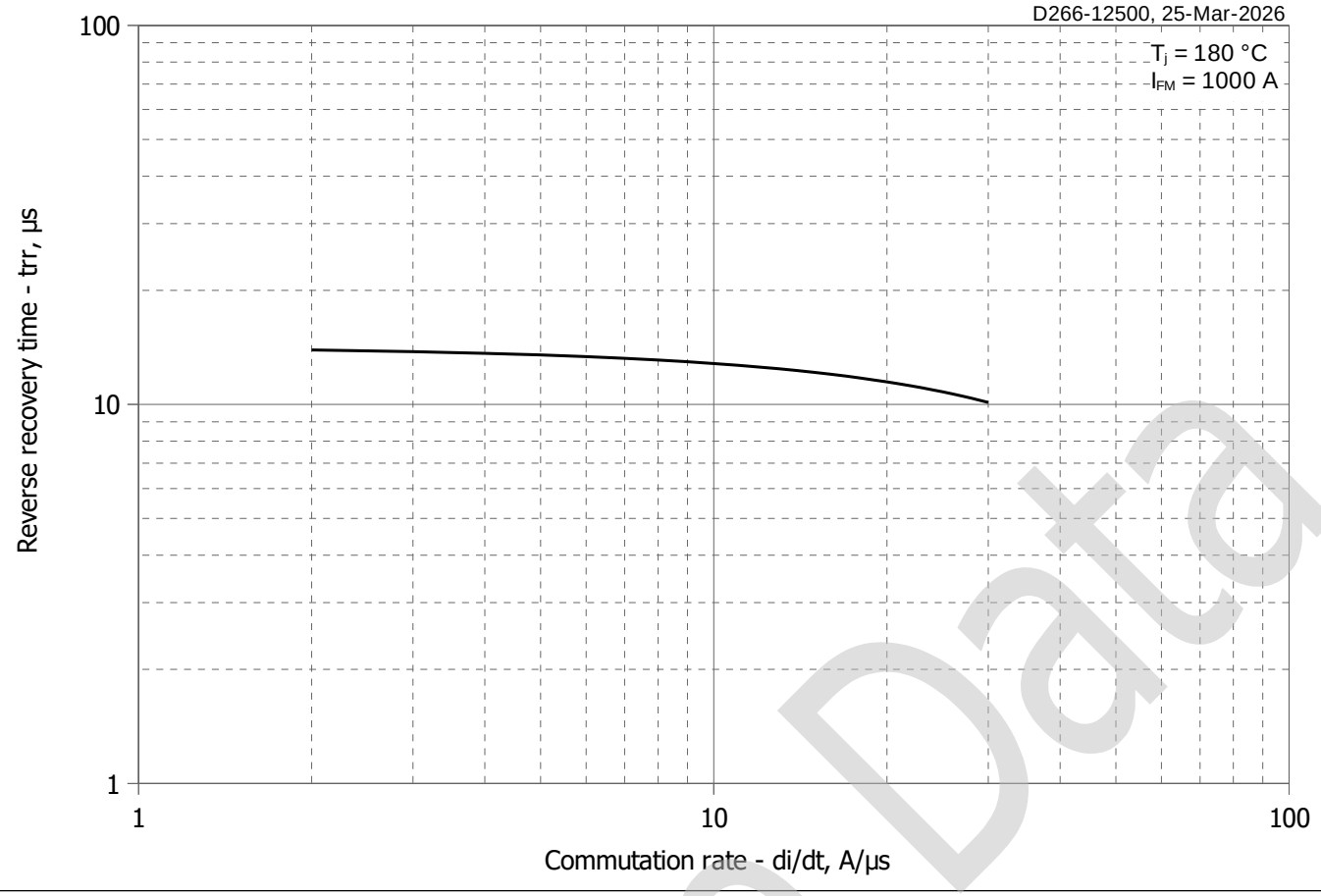


Fig 5 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

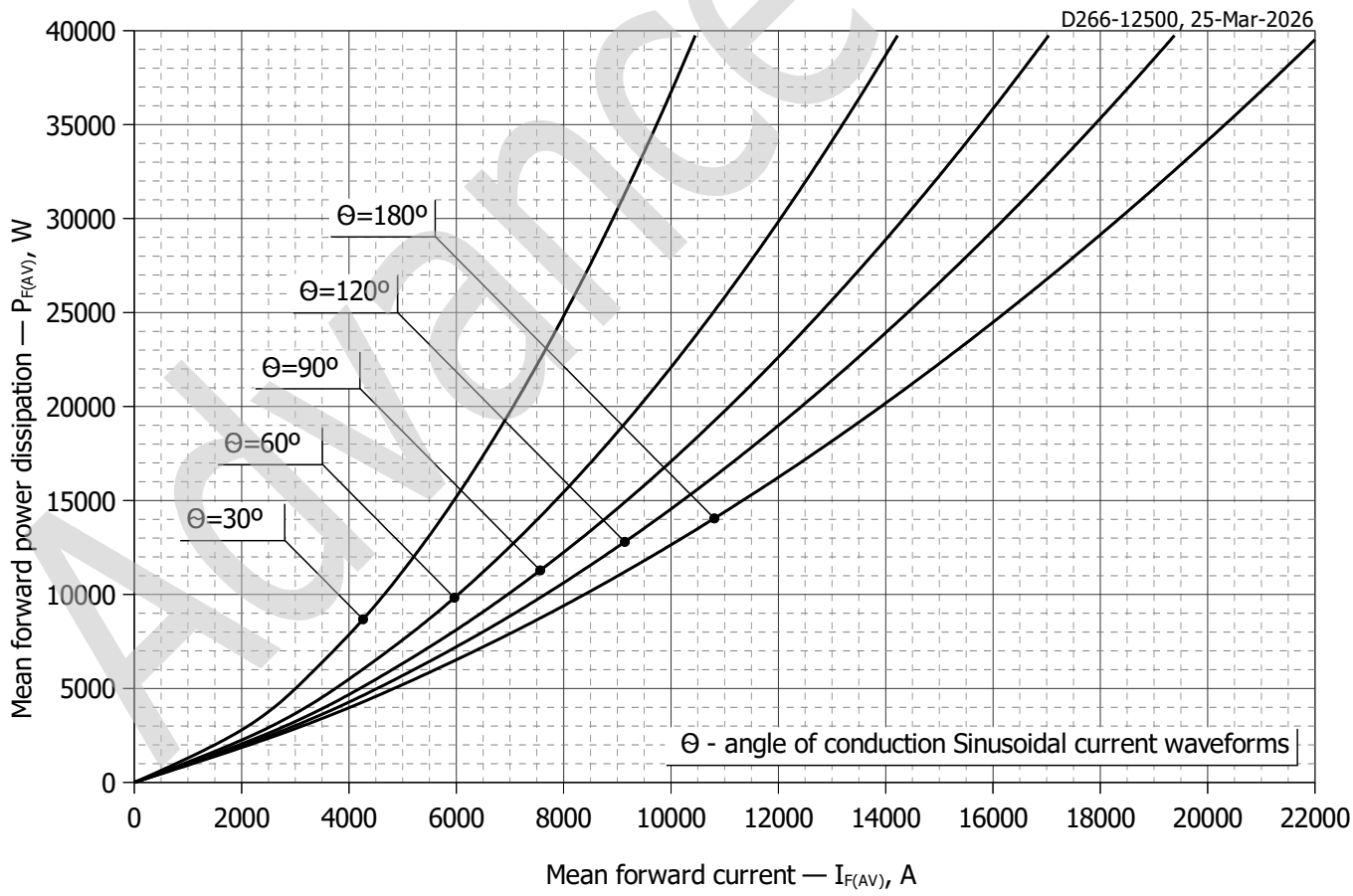


Fig 6 – Mean forward power dissipation P_{FAV} vs. Mean forward current I_{FAV} for sinusoidal current waveforms at different conduction angles (f=50Hz, DSC)

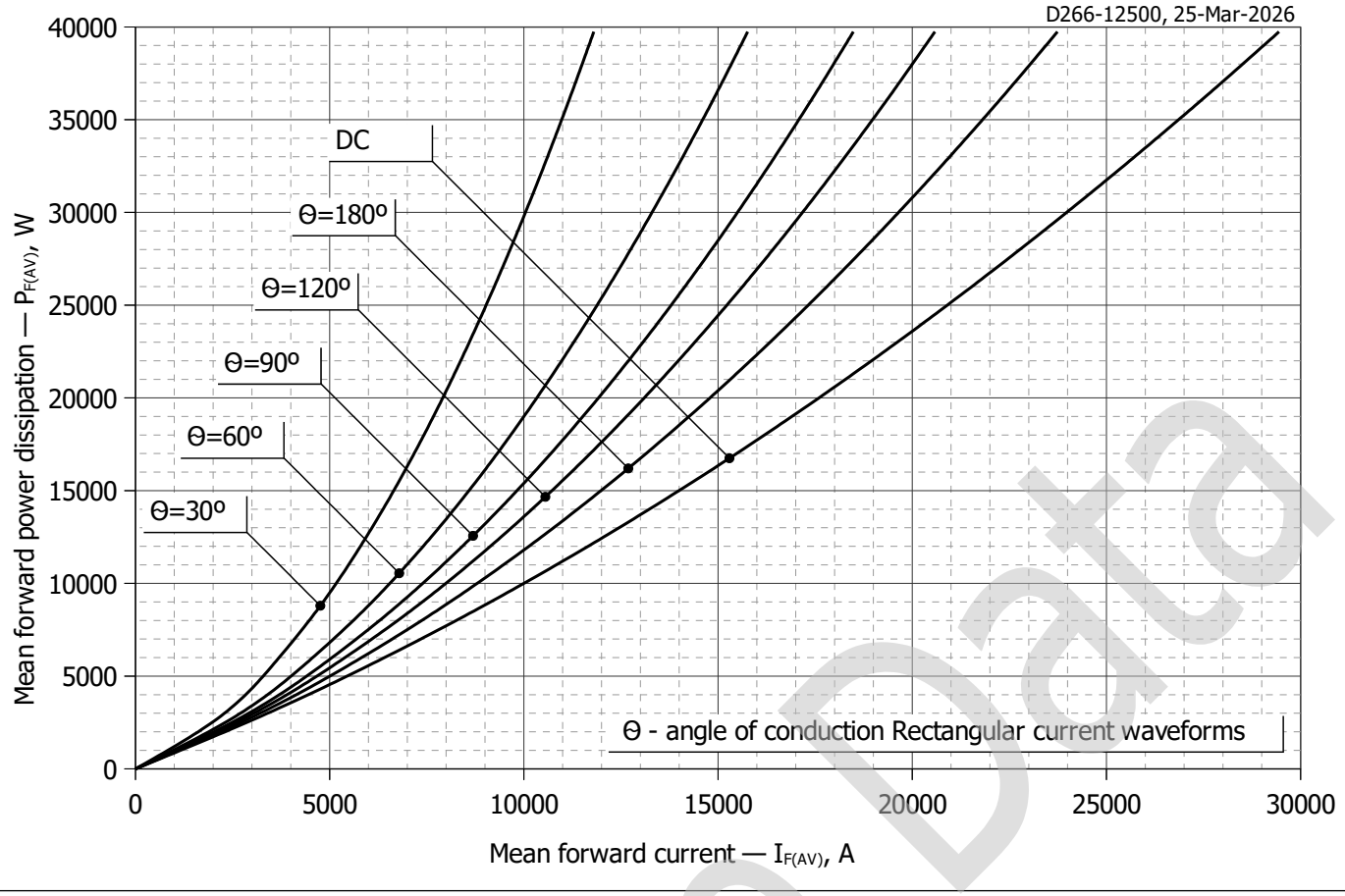


Fig 7 – Mean forward power dissipation P_{FAV} vs. Mean forward current I_{FAV} for rectangular current waveforms at different conduction angles and for DC (f=50Hz, DSC)

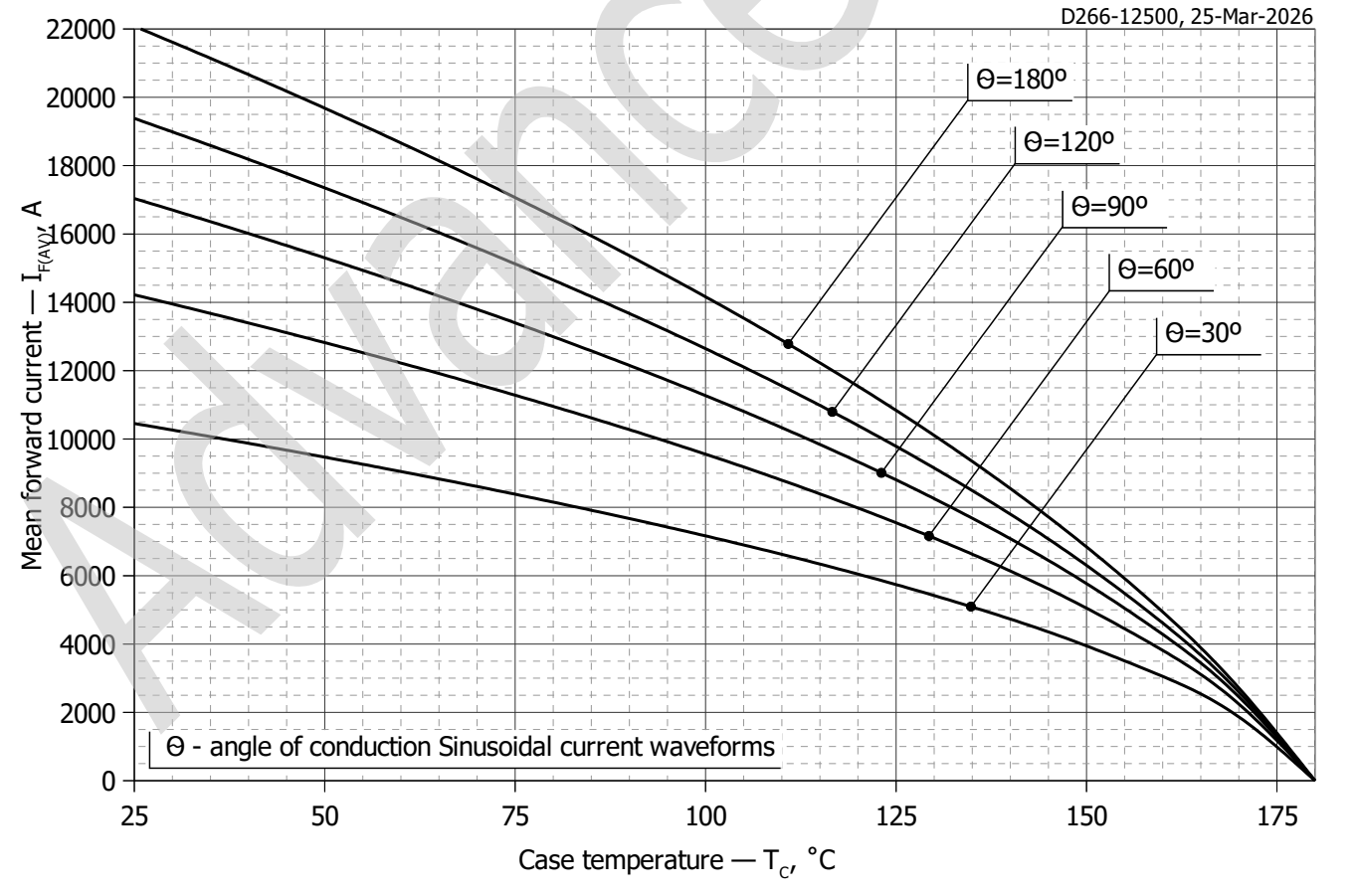


Fig 8 - Mean forward current I_{FAV} vs. Case temperature T_C for sinusoidal current waveforms at different conduction angles (f=50Hz, DSC)

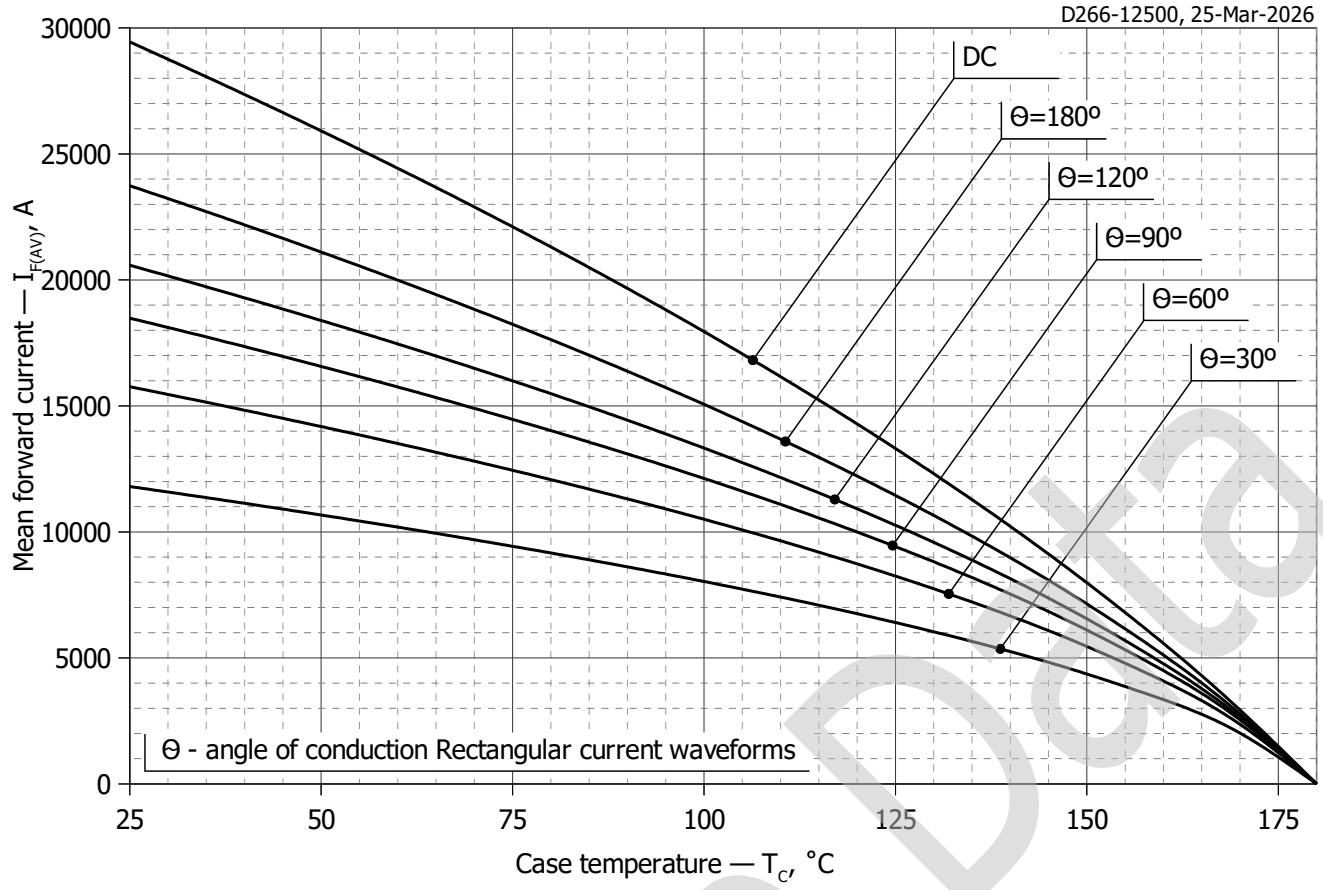


Fig 9 – Mean forward current I_{FAV} vs. Case temperature T_C for rectangular current waveforms at different conduction angles and for DC (f=50Hz, DSC)

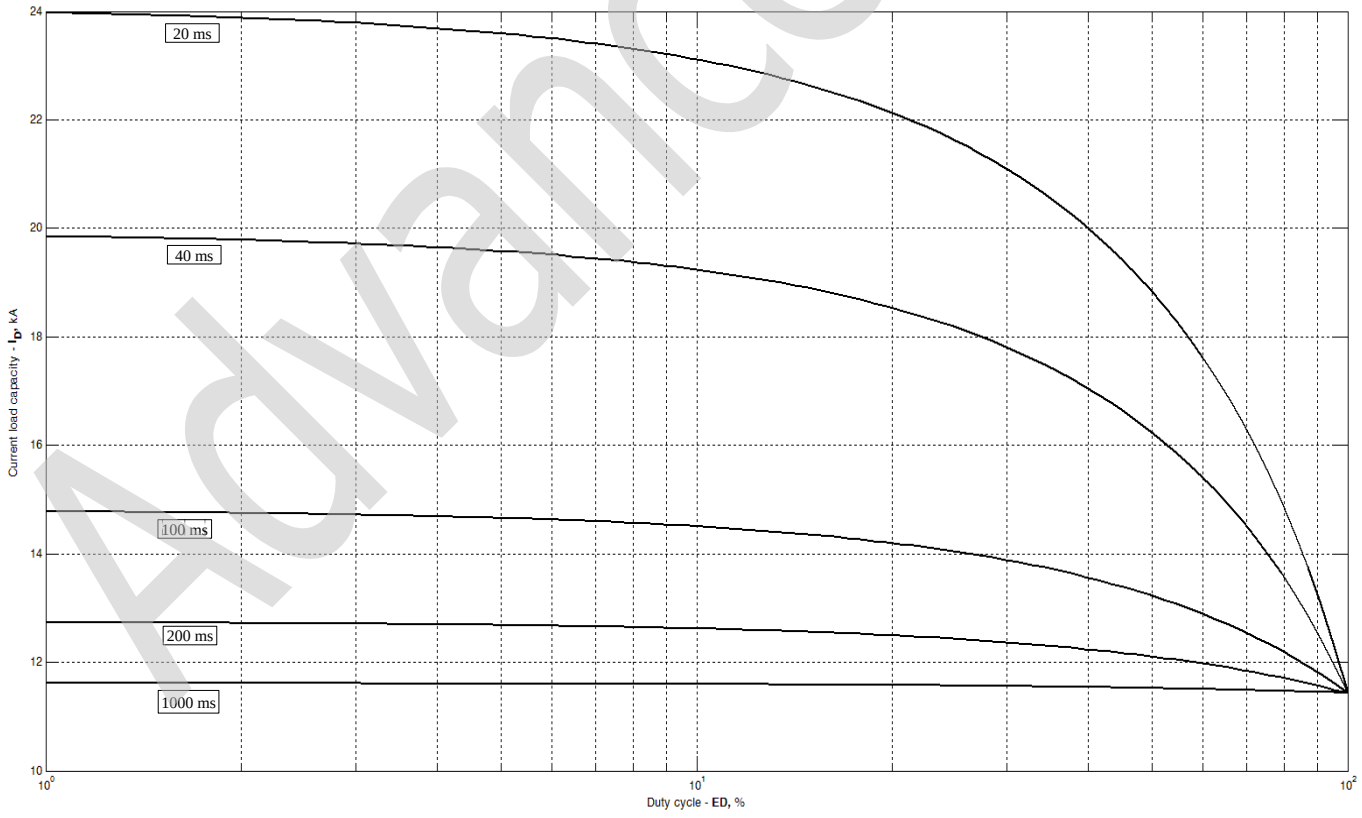


Fig 10 – Current load capability (f=1000 Hz, square wave, ΔT_j = 40 °C)

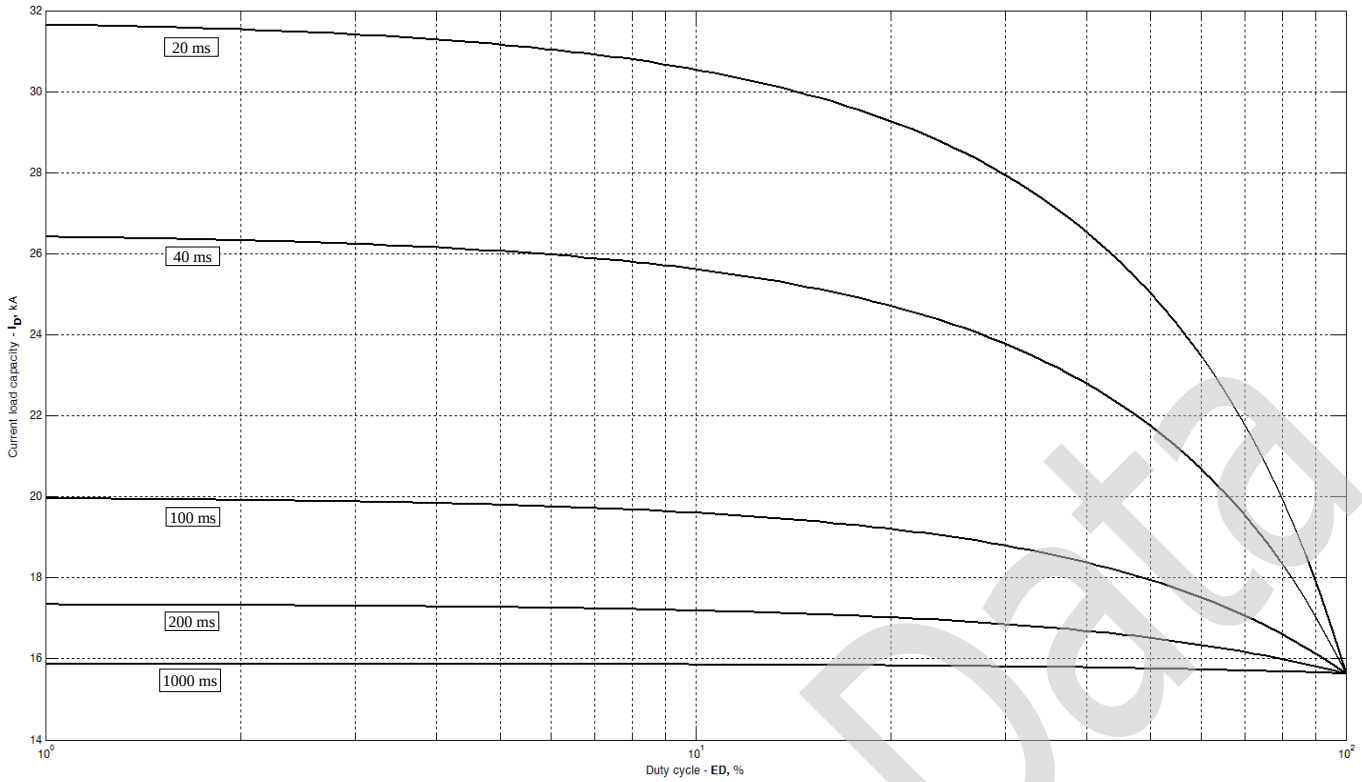


Fig 11 – Current load capability (f=1000 Hz, square wave, ΔT_j = 60 °C)

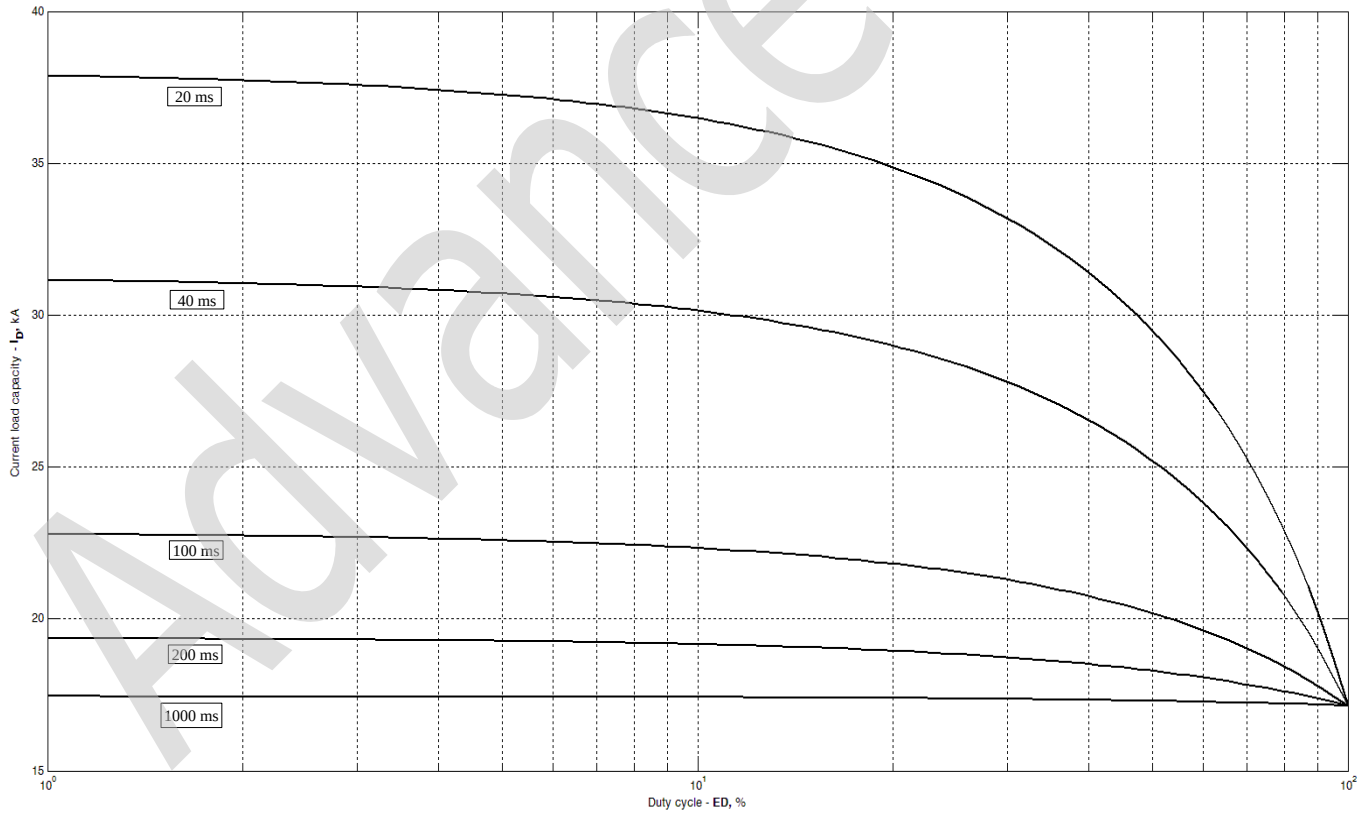


Fig 12 – Current load capability (f=1000 Hz, square wave, ΔT_j = 70 °C)

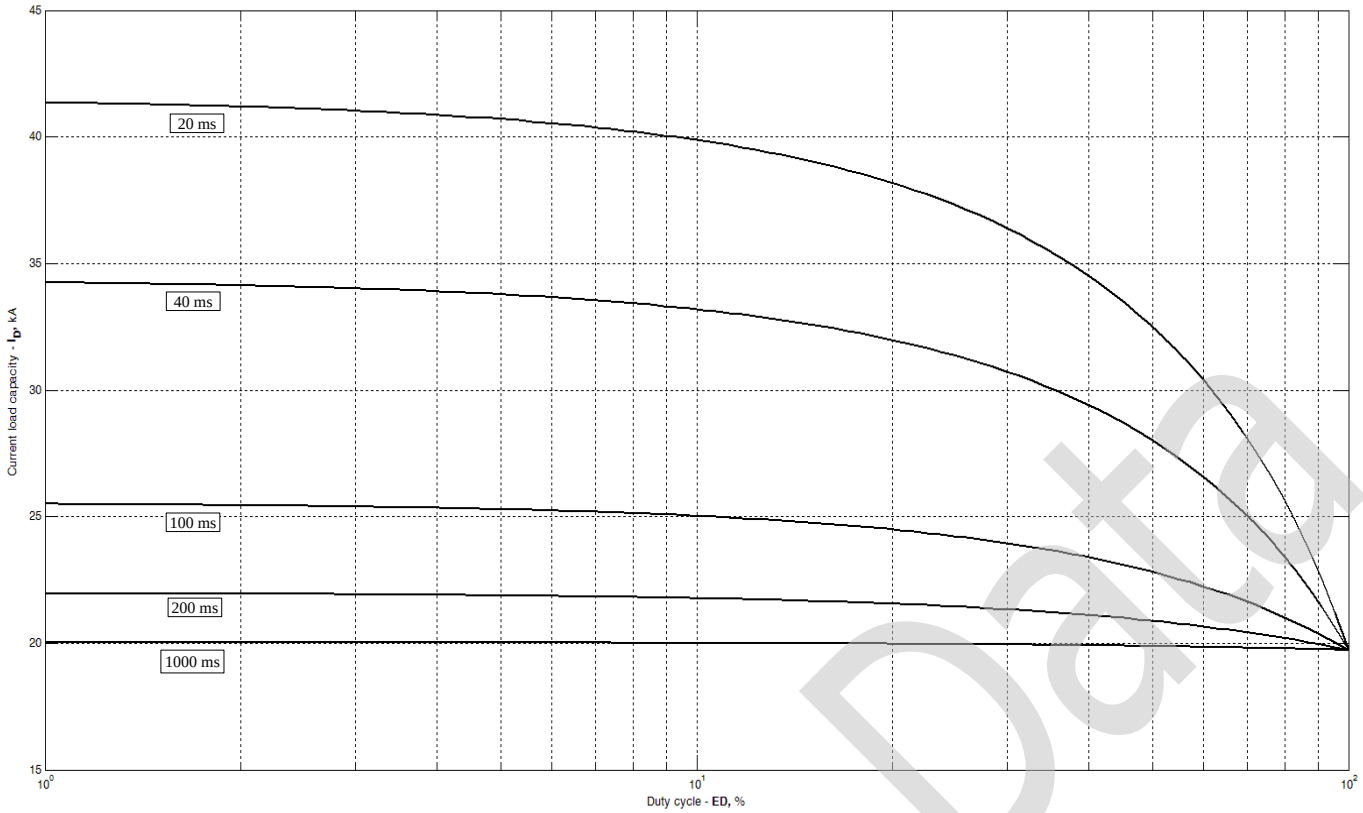


Fig 13 – Current load capability (f=1000 Hz, square wave, ΔT_j = 80 °C)

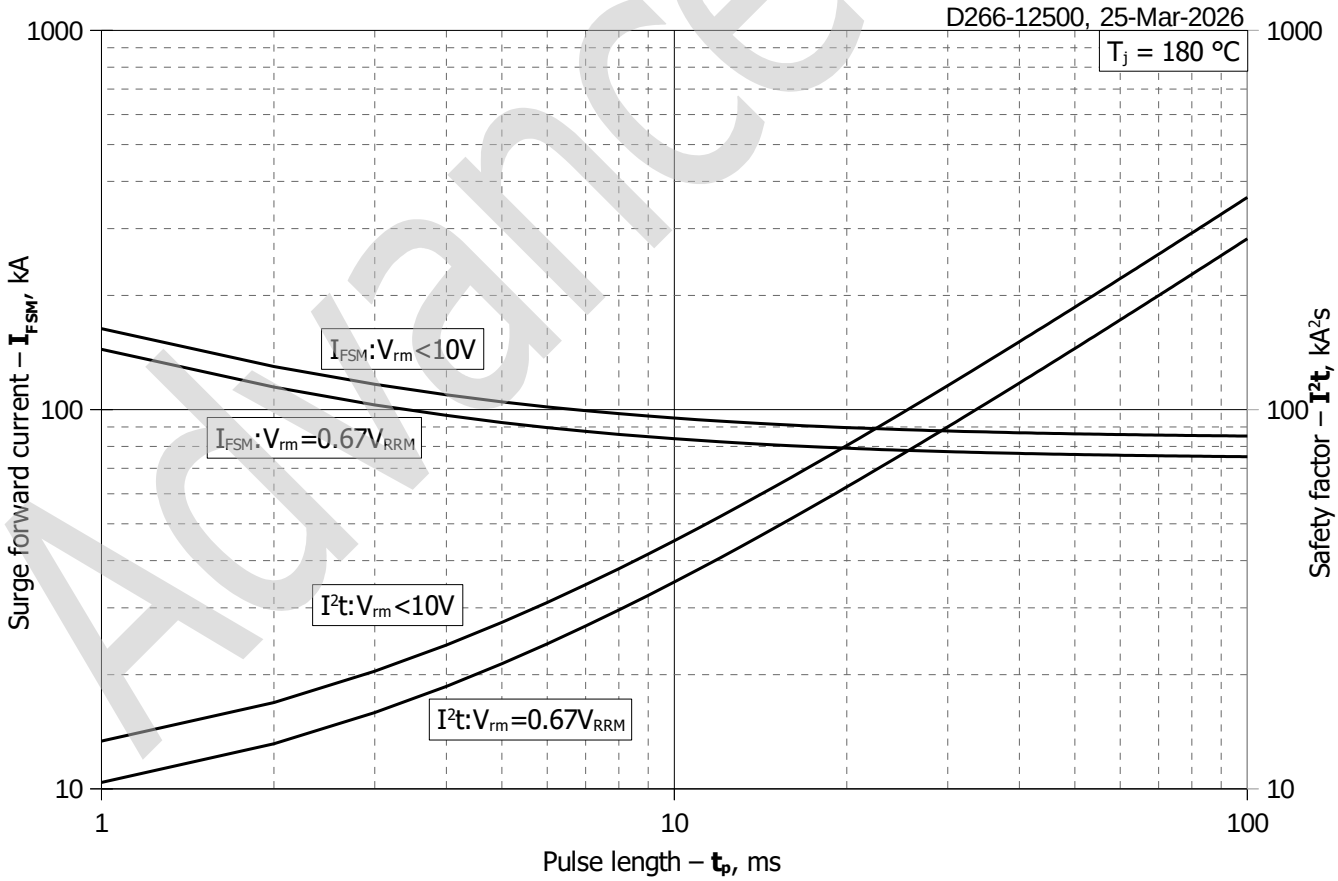


Fig 14 – Maximum surge forward current I_{FSM} and safety factor I^2t vs. pulse length t_p

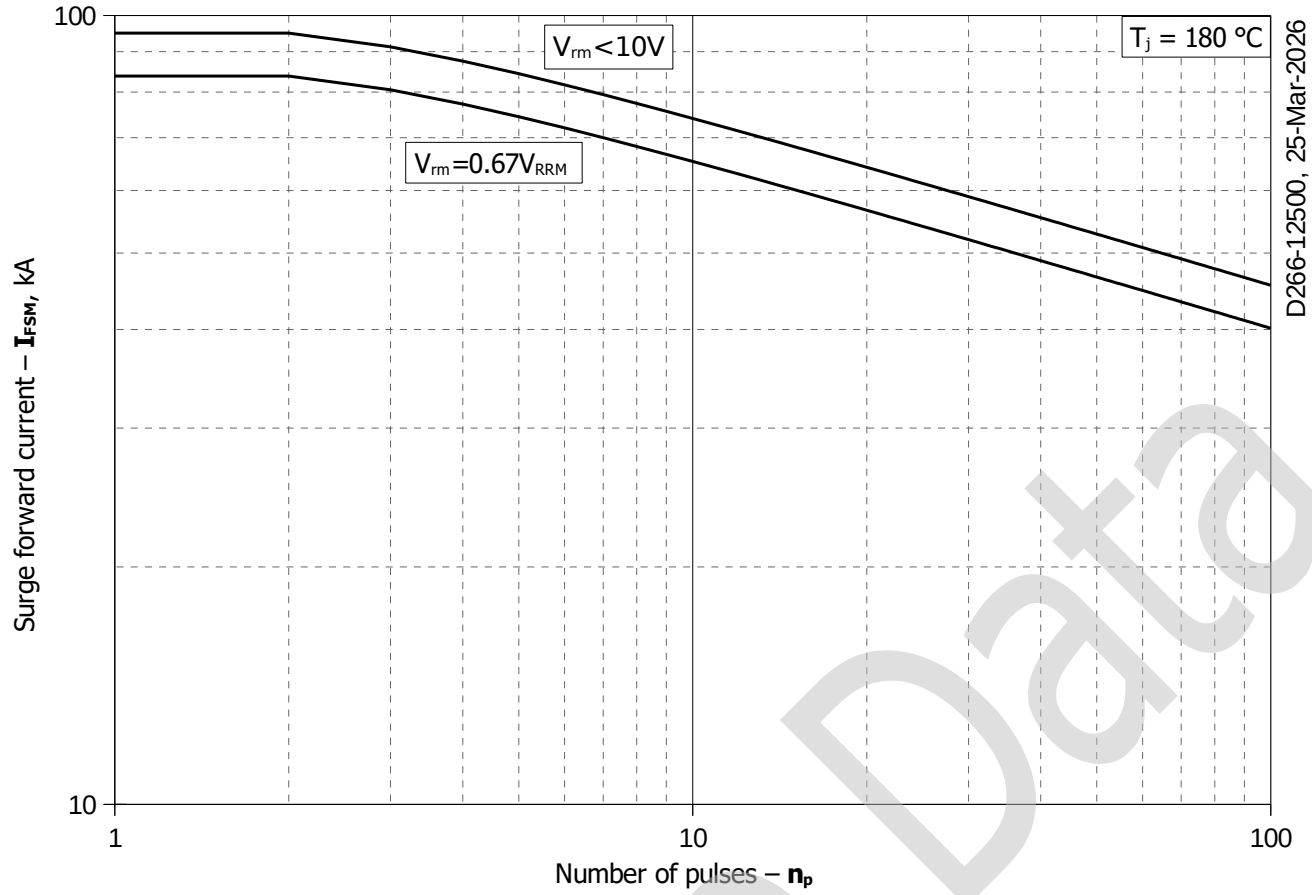


Fig 15 – Maximum surge forward current I_{FSM} vs. number of pulses n_p

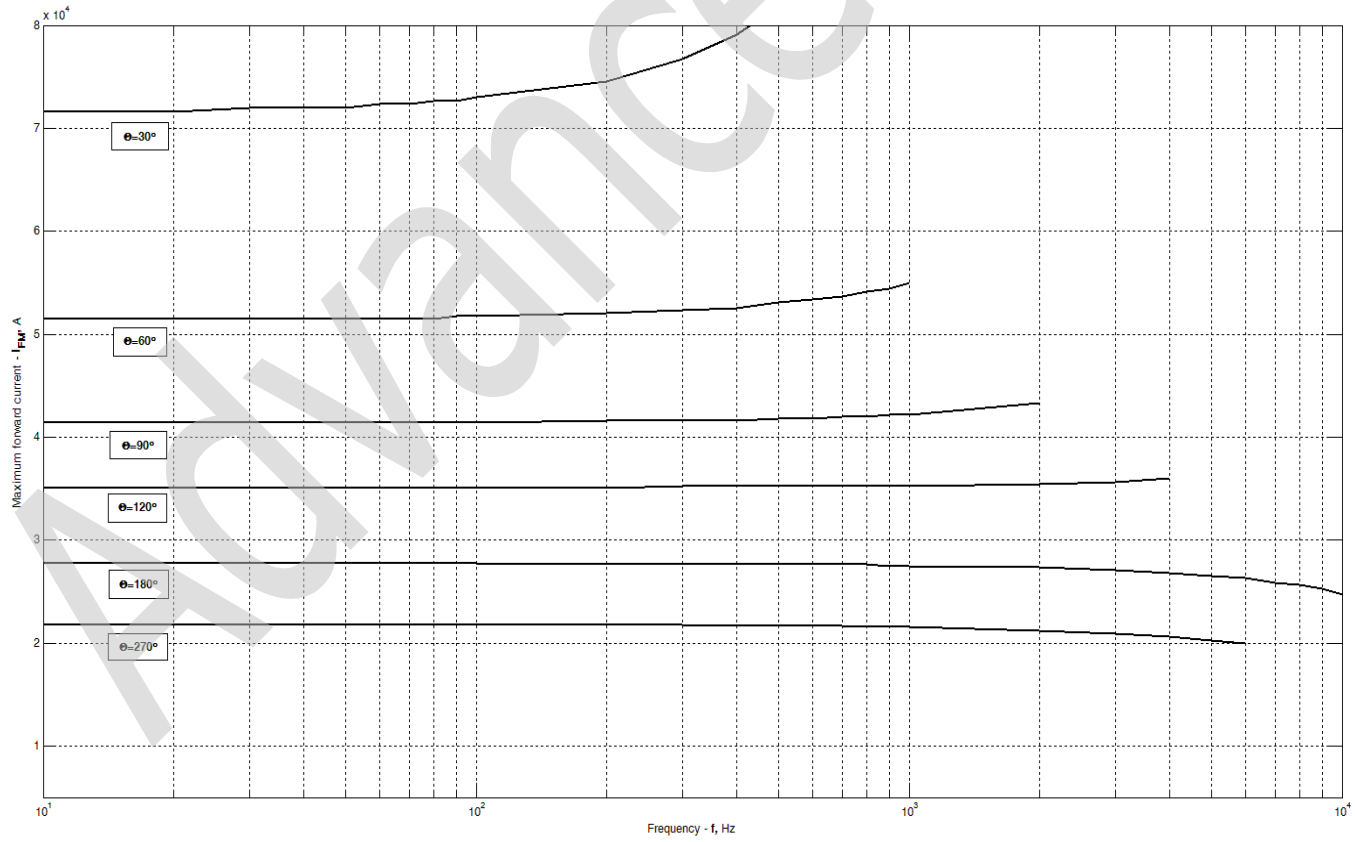


Fig 16 –Maximum forward current vs. frequency, trapezoidal waveform, T_C=85 °C, di_F/dt=±500 A/µs, V_R=100 V

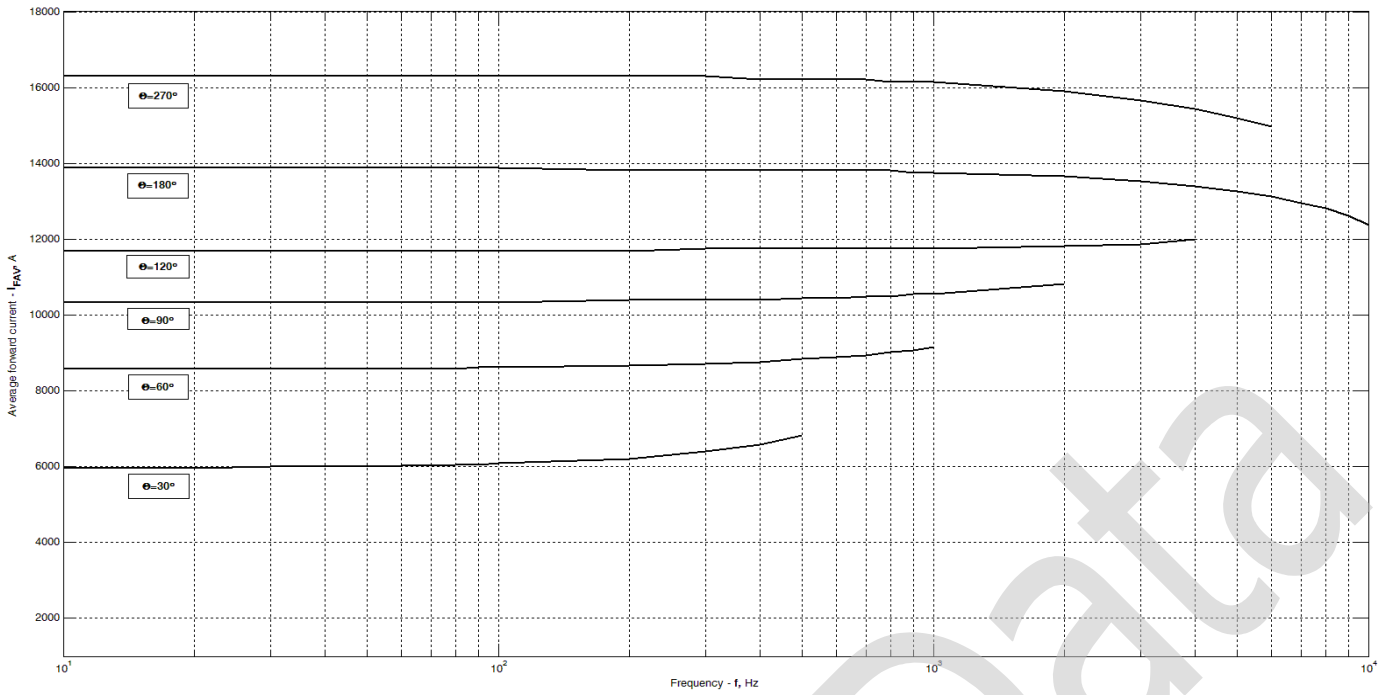


Fig 17 –Average forward current vs. frequency, trapezoidal waveform, T_C=85 °C, di_F/dt=±500 A/µs, V_R=100 V